

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 – 12. (cancelled)

13. (currently amended): A chemical mechanical polishing method, comprising simultaneously removing by polishing a conductive layer, a silicon oxide layer and a silicon nitride layer using a polishing slurry comprising an abrasive, deionized water, a pH controlling agent, a choline derivative, and polyethylene imine having a molecular structure of $[-CH_2CH_3N(CH_2CH_2NH_2)-]_x[-CH_2CH_2NH_2-]_y$, where one of x and y is a positive integer, and the other of x and y is 0 or a positive integer, and wherein the choline derivative is choline chloride.

14. (previously presented): The method of claim 13, wherein the silicon oxide layer is one selected from the group consisting of a borophosphorosilicate glass (BPSG), a phosphosilicate glass (PSG), a borosilicate glass (BSG), a high density plasma (HDP) silicon oxide layer, an undoped silicate glass (USG), a high thermal (HT)-USG, and a plasma enhanced (PE)-silicon oxide layer.

15. (original): The method of claim 13, wherein the silicon nitride layer is a dielectric material having a basic formula of Si_3N_4 .

16. (original): The method of claim 13, wherein the polyethylene imine comprises more than 0.02 wt% of the polishing slurry.

17 – 20. (cancelled)

21. (previously presented): The method of claim 13, where both of x and y are positive integers.